

Fig. 1

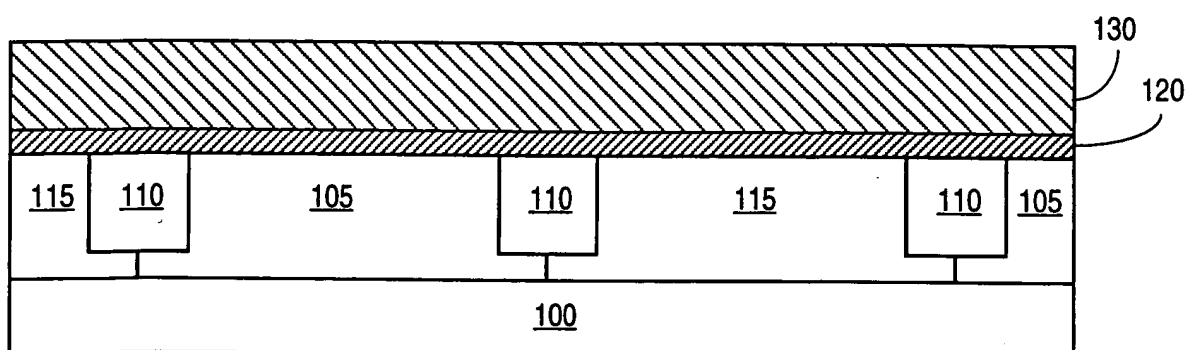


Fig. 2

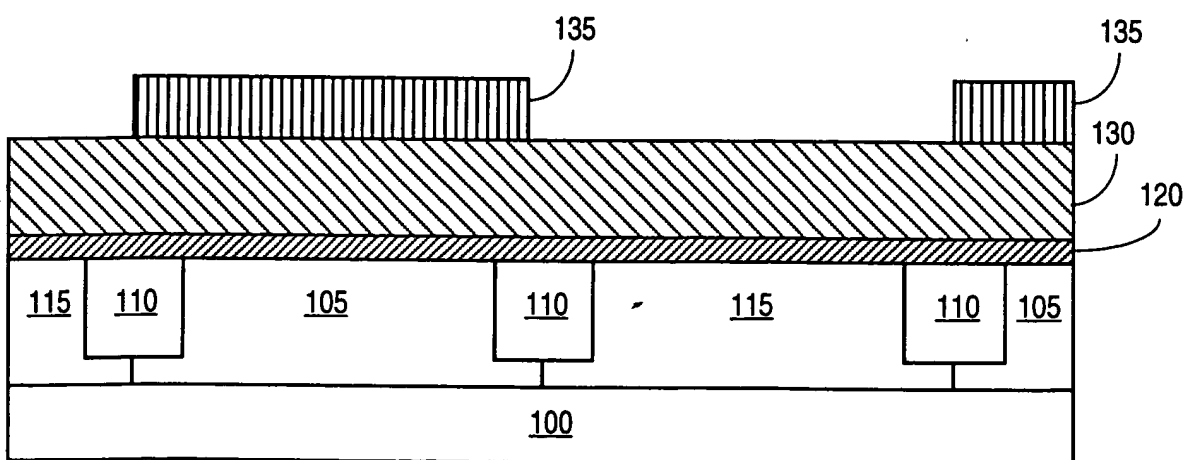


Fig. 3

0051705-030200

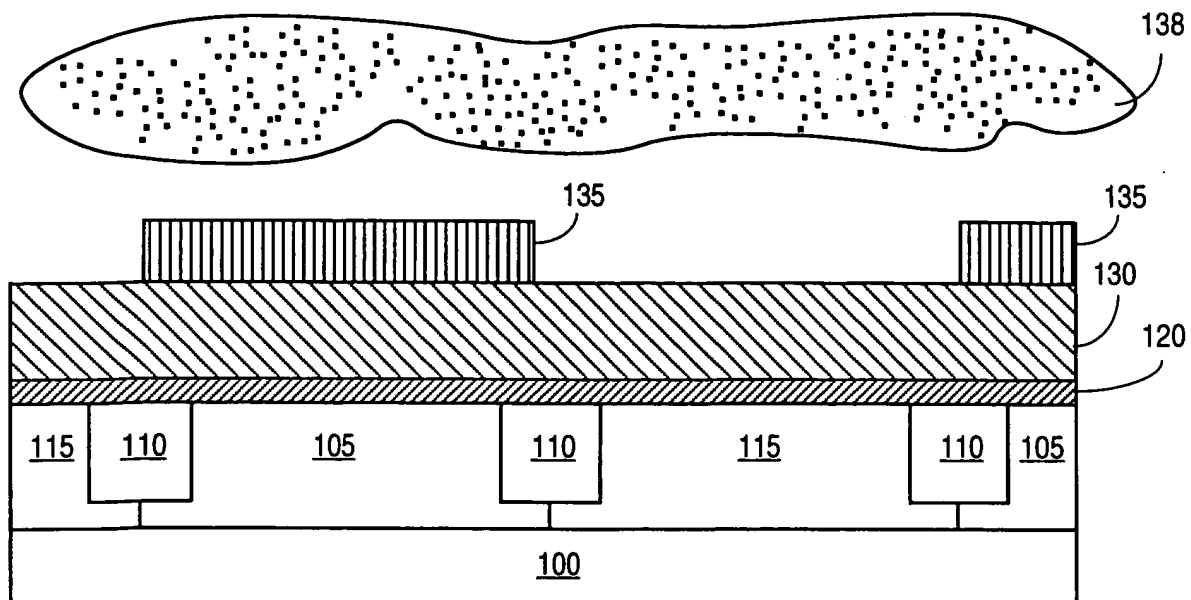


Fig. 4

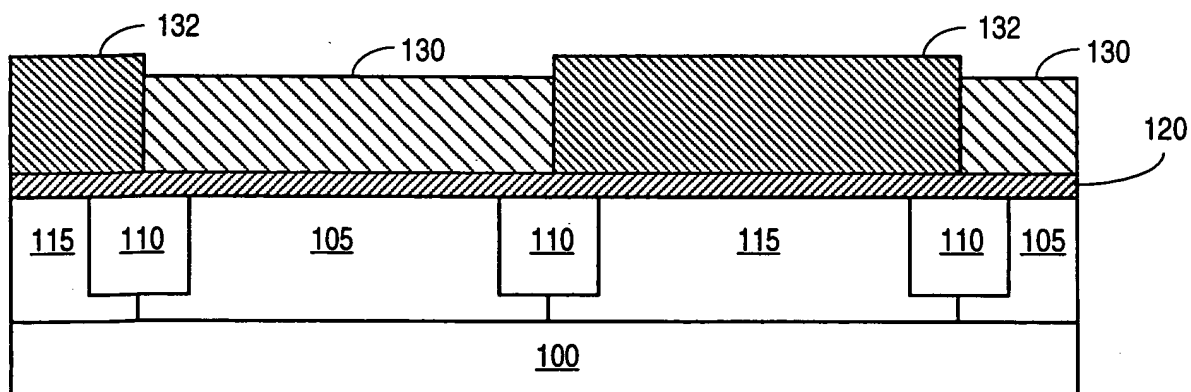


Fig. 5

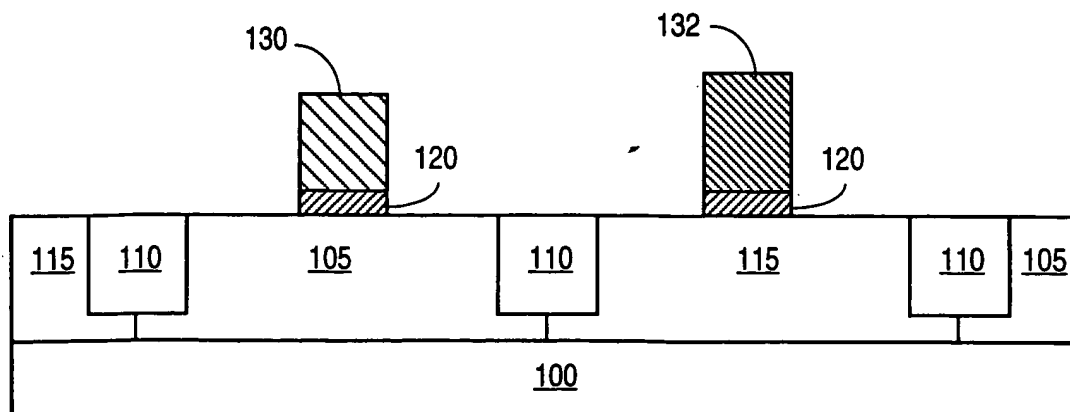


Fig. 6

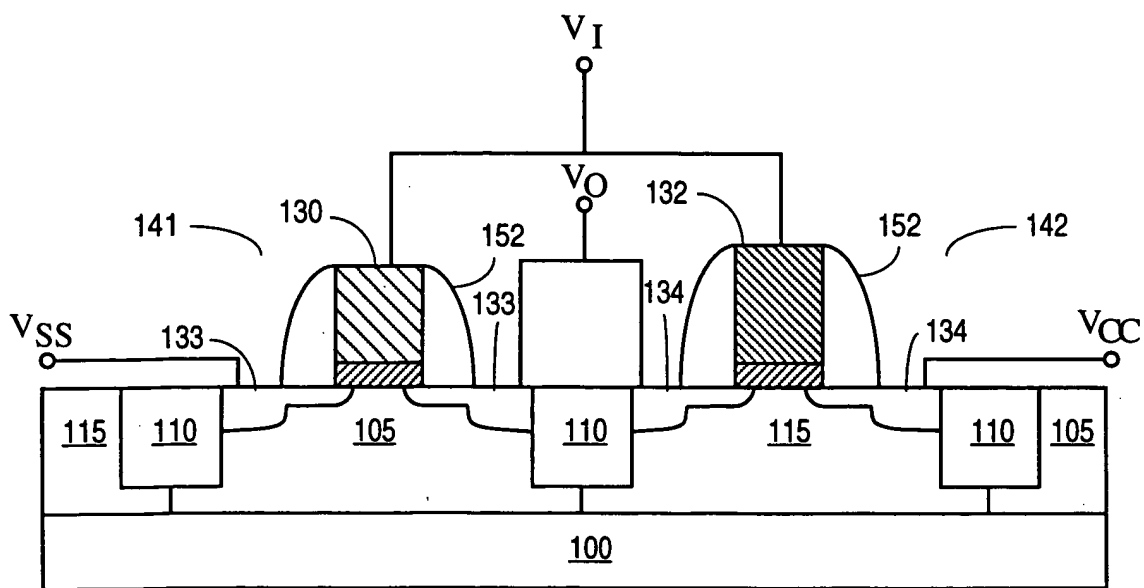


Fig. 7

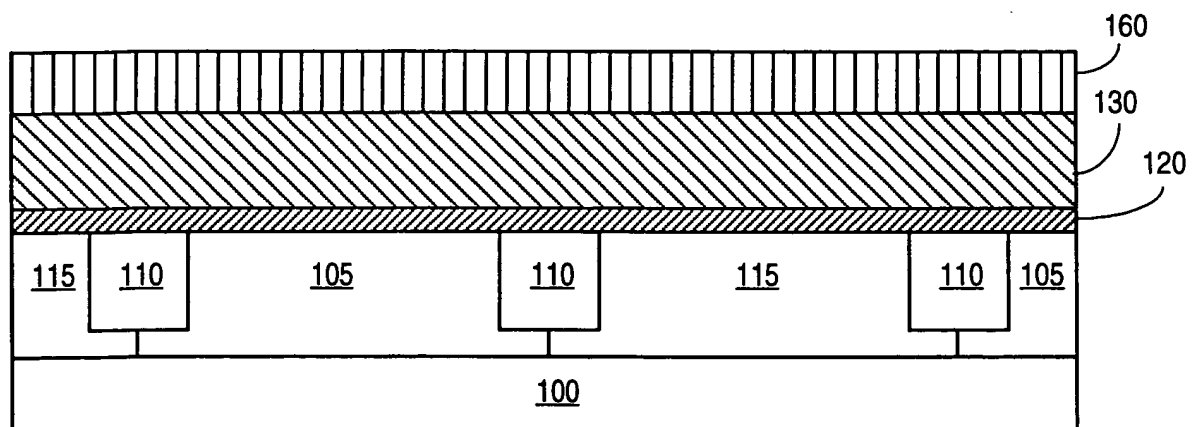


Fig. 8

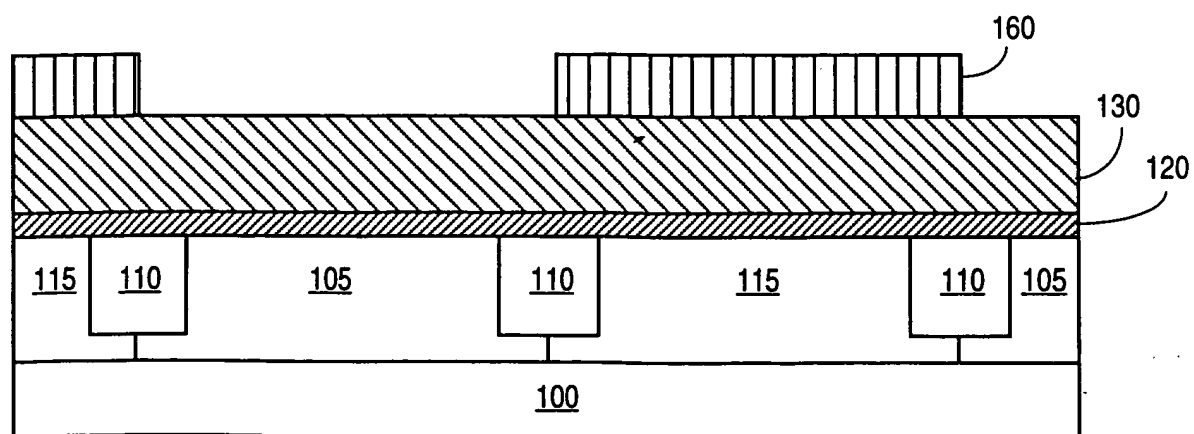


Fig. 9

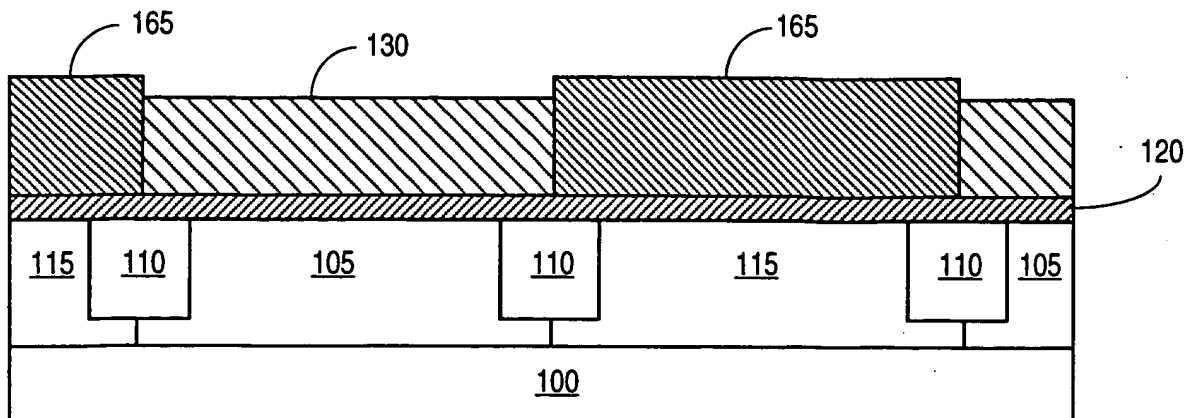


Fig. 10

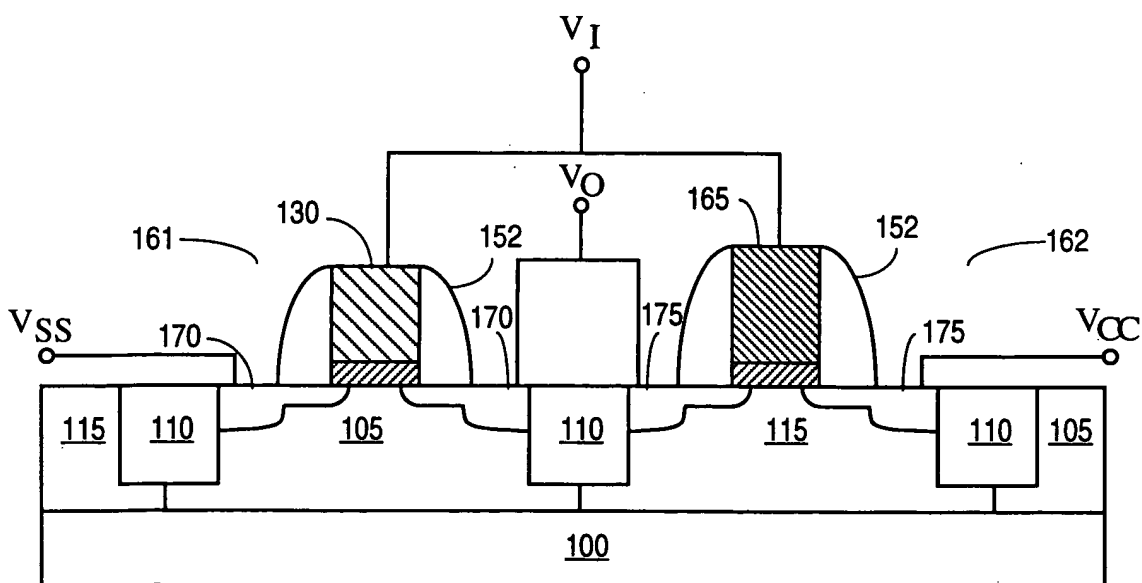


Fig. 11

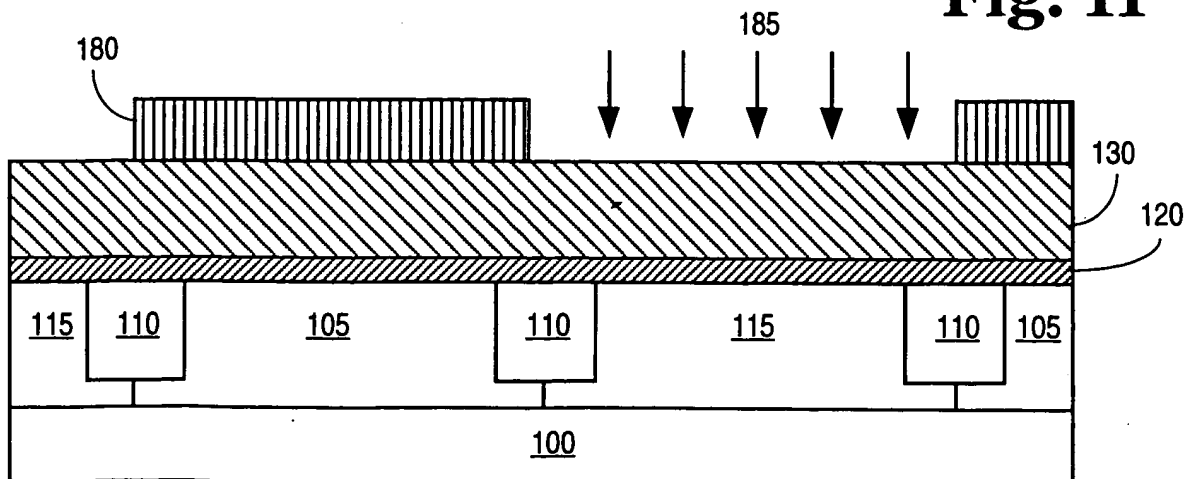


Fig. 12

A cross-sectional view of a semiconductor device. A substrate 100 is at the bottom. Above it is a layer with a pattern of rectangular blocks 110 and spaces 115. A thin, uniform layer 120 covers the entire surface. On top of layer 120 is a layer 130, which has a raised rectangular portion 190 in the center.

Fig. 14